

Amendments to the Specification

Kindly amend the specification as follows:

Page 1, between the title and the heading "**BACKGROUND OF THE INVENTION**", insert

--CROSS REFERENCE TO RELATED APPLICATIONS

This is a continuation application of application Serial No. 10/283,189, filed October 30, 2002, which is hereby incorporated by reference in its entirety for all purposes.--

Please replace the paragraph beginning on page 8, line 9 with the following amended paragraph:

Then, a second heat treatment is carried out. That is, the titanium silicide layers 131, 132, 133 are heated to a temperature of 850°C. Thereby, the TiSi layer or the Ti₂Si layer of the titanium silicide layers 131, 132, 133 are respectively changed into TiSi₂ layers 141, 142, 143, as shown in Fig.5. That is, the ~~titanium~~ titanium layers (TiSi₂) 141, 142, 143 have a crystalline structure of C54. Therefore, as resistance of the titanium silicide layers 141, 142, 143 become low, resistance of the gate electrode 11 and the active regions can be reduced.

Please replace the paragraph beginning on page 14, line 8 with the following amended paragraph:

Then, the titanium nitride layer 23 and the titanium layer ~~[[32]]~~ 21 which is not reacted with silicon in the single silicon layer 5 or the gate electrode 11, is removed using mixture liquid of an ammonia solution and a hydrogen peroxide solution, as shown in Fig. 9.

Please replace the paragraph beginning on page 14, line 12 with the following amended paragraph:

Then, a second heat treatment is carried out. That is, the titanium silicide layers 31, 32, 33 are heated to a temperature of 850°C. Thereby, the TiSi layer or the Ti₂Si layer of the titanium silicide layers 31, 32, 33 are respectively changed into TiSi₂ layers 41, 42, 43, as shown in Fig.10. That is, the ~~titanium~~ titanium layers (TiSi₂) 41, 42, 43 have a crystalline structure of C54. Therefore, as resistance of the titanium silicide layers 41, 42, 43 become low, resistance of the gate electrode 11 and the active regions can be reduced. As thickness of the titanium silicide layers 42, 43 which are formed in the active region (the source and drain regions) is 30nm, portions of the titanium silicide layers 42, 43 do not reach to the silicon oxide layer 3.

Please replace the abstract with the following amended abstract:

A method for fabricating semiconductor devices includes forming a protective

layer ~~is formed~~ on a metallic layer prior to forming a metallic silicide layer, ~~[[and]]~~ the protective layer ~~[[has]]~~ having a thickness ~~thicker~~ greater than that of the metallic layer.